

MOSFET - Power, Single N-Channel

40 V, 1.1 mΩ, 240 A

FDBL9406L-F085

Features

- Small Footprint (TOLL) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D 240 A
		$T_C = 100^\circ\text{C}$	P_D 150 W
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	P_D 300 W
		$T_C = 100^\circ\text{C}$	P_D 150 W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D 43 A
		$T_A = 100^\circ\text{C}$	I_D 31 A
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	P_D 3.5 W
		$T_A = 100^\circ\text{C}$	P_D 1.7 W
Pulsed Drain Current	$T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM} 2755	A
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	100	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 85 \text{ A}; L = 60 \mu\text{H}$)	E_{AS}	217	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

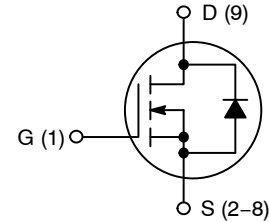
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

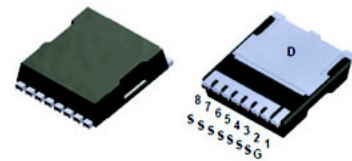
Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	0.5	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	43	$^\circ\text{C}/\text{W}$

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted. Current is limited by bondwire configuration.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
40 V	1.1 mΩ @ 10 V	80 A
	1.78 mΩ @ 4.5 V	

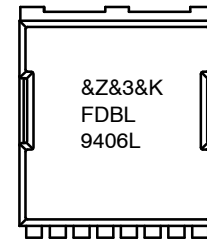


N-CHANNEL MOSFET



H-PSOF8L CASE 100CU

MARKING DIAGRAM



- &Z = Assembly Plant Code
- &3 = Numeric Date Code
- &K = Lot Code
- FDBL9406L = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

FDBL9406L–F085

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	40	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$		-	19.3	-	mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, T_J = 25^\circ\text{C}$	-	-	1	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, T_J = 175^\circ\text{C}$	-	-	1	mA
Zero Gate Voltage Drain Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1	1.9	3	V
Threshold Temperature Coefficient	$V_{GS(th)}/T_J$		-	-6.5	-	mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 80\text{ A}$	-	0.9	1.1	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 40\text{ A}$	-	1.25	1.78	

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 20\text{ V}$	-	8600	-	pF
Output Capacitance	C_{oss}		-	2380	-	pF
Reverse Transfer Capacitance	C_{rss}		-	106	-	pF
Gate Resistance	R_g	$V_{GS} = 0.5\text{ V}, f = 1\text{ MHz}$	-	2	-	Ω
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 32\text{ V}, I_D = 80\text{ A}$	-	58	-	nC
		$V_{GS} = 10\text{ V}, V_{DS} = 32\text{ V}, I_D = 80\text{ A}$	-	121	-	
Threshold Gate Charge	$Q_{g(th)}$	$V_{GS} = 0\text{ to }1\text{ V}$	-	7	-	
Gate-to-Source Gate Charge	Q_{gs}	$V_{DD} = 32\text{ V}, I_D = 80\text{ A}$	-	26	-	
Gate-to-Drain "Miller" Charge	Q_{gd}		-	19	-	
Plateau Voltage	V_{GP}		-	3.2	-	V

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, I_D = 80\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$	-	22	-	ns
Turn-On Rise Time	t_r		-	22	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	134	-	ns
Turn-Off Fall Time	t_f		-	44	-	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

Source-to-Drain Diode Voltage	V_{SD}	$I_{SD} = 80\text{ A}, V_{GS} = 0\text{ V}$	-	0.81	1.25	V
		$I_{SD} = 40\text{ A}, V_{GS} = 0\text{ V}$	-	0.77	1.2	V
Reverse Recovery Time	T_{RR}	$V_{GS} = 0\text{ V}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}$ $I_S = 80\text{ A}$	-	77	-	ns
Charge Time	t_a		-	38	-	
Discharge Time	t_b		-	39	-	
Reverse Recovery Charge	Q_{RR}		-	95	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

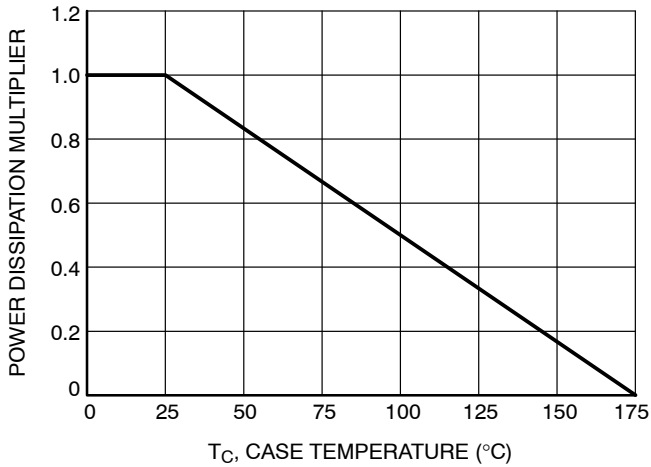


Figure 1. Normalized Power Dissipation vs. Case Temperature

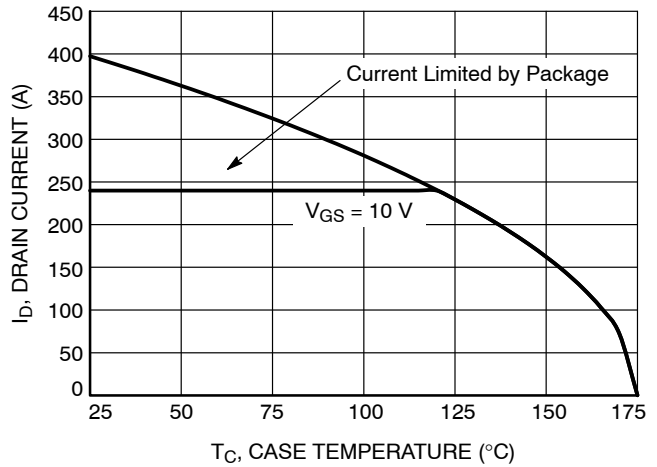


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

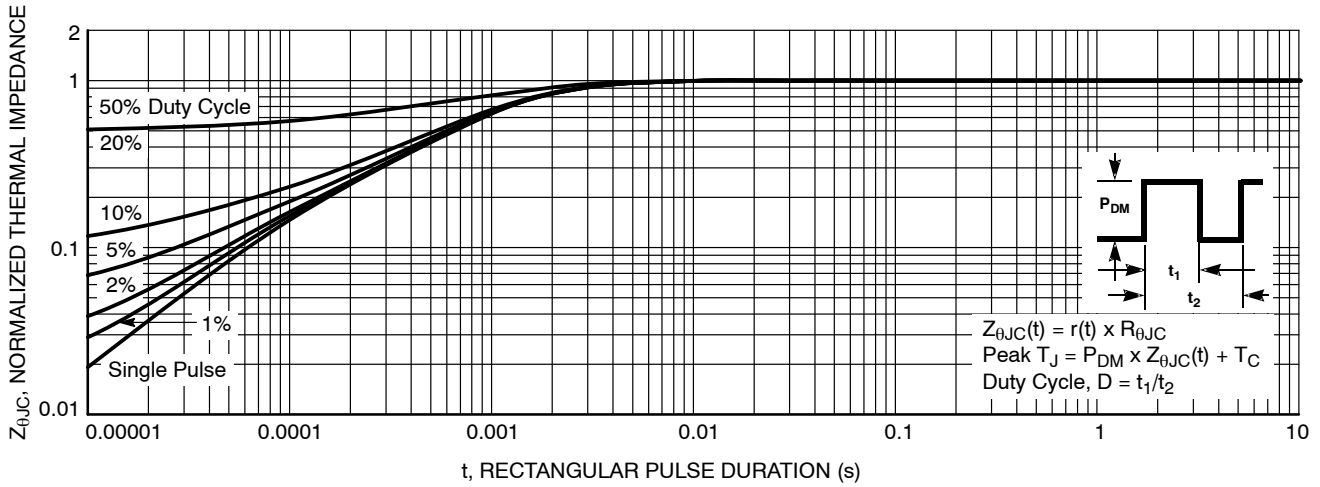


Figure 3. Normalized Maximum Transient Thermal Impedance

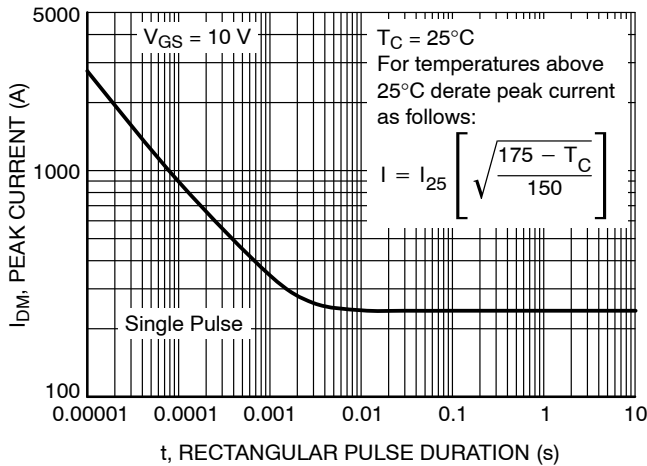


Figure 4. Peak Current Capability

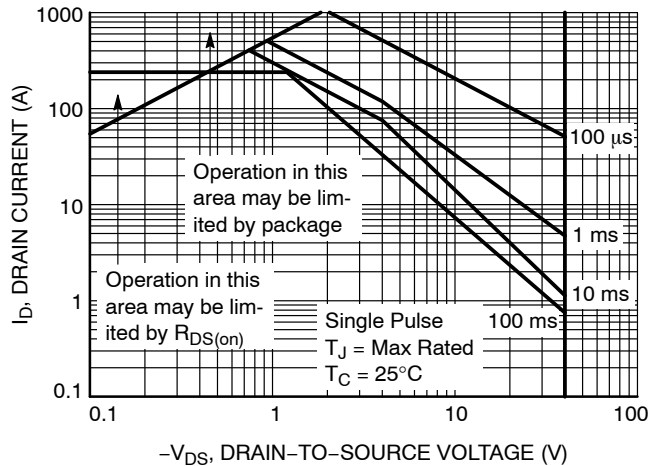


Figure 5. Forward Bias Safe Operating Area

TYPICAL CHARACTERISTICS

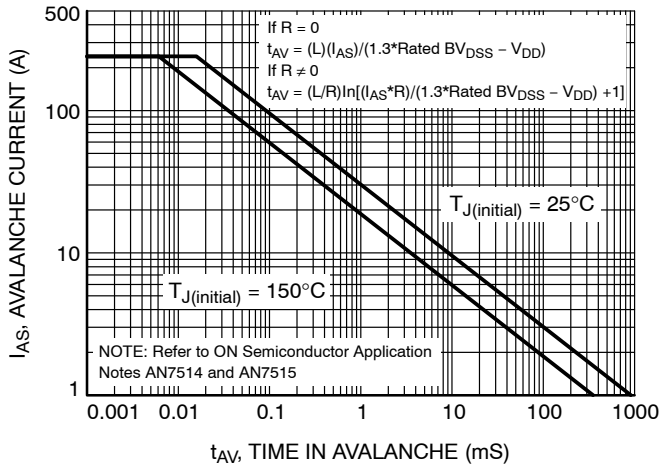


Figure 6. Unclamped Inductive Switching Capability

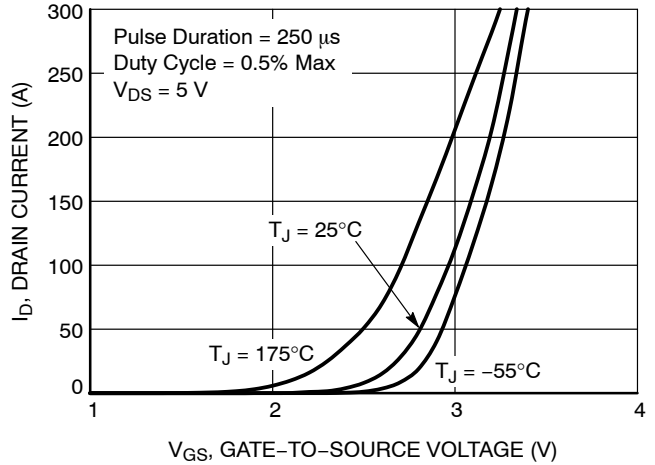


Figure 7. Transfer Characteristics

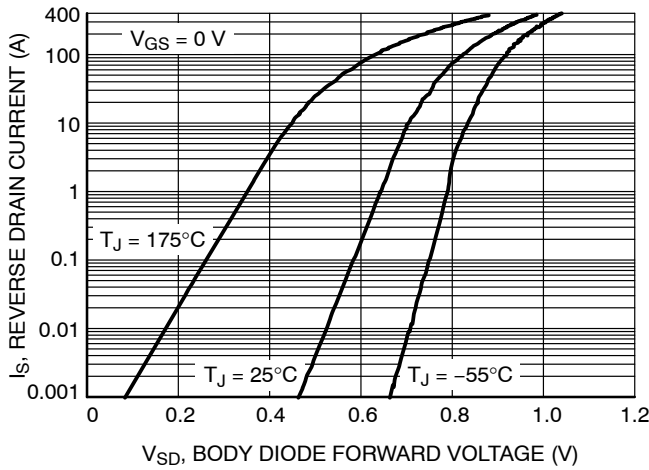


Figure 8. Forward Diode Characteristics

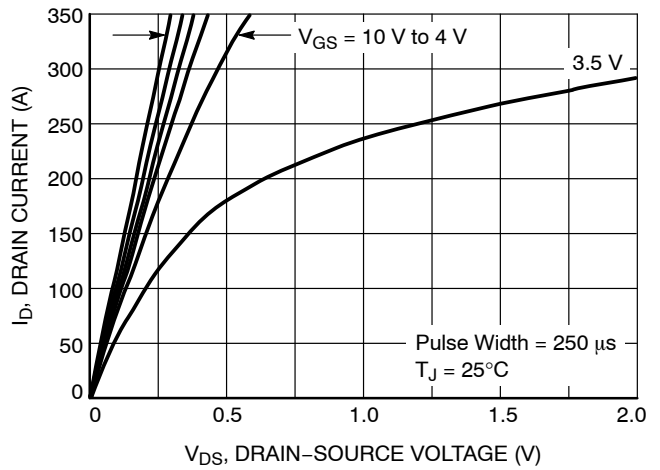


Figure 9. Saturation Characteristics

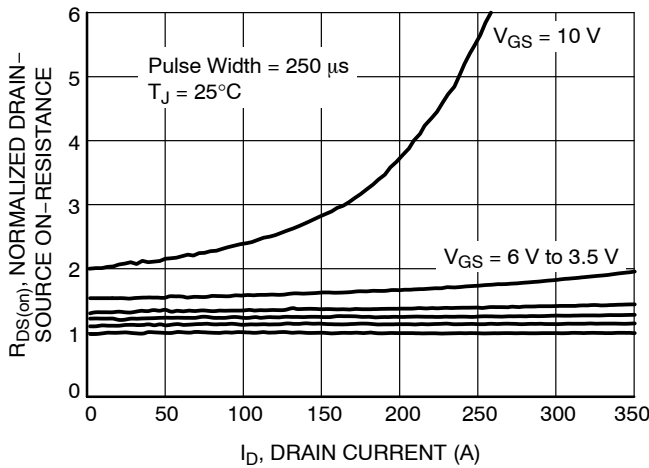


Figure 10. Normalized $R_{DS(on)}$ vs. Drain Current

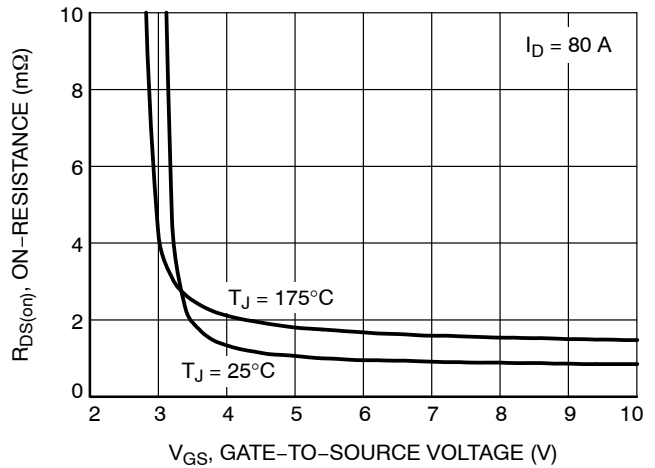


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

TYPICAL CHARACTERISTICS

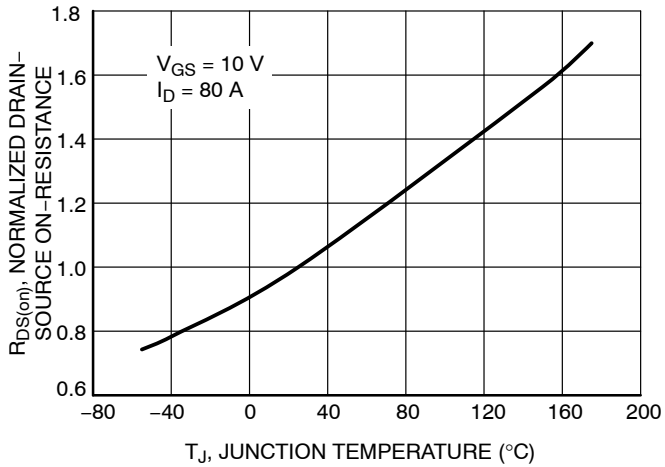


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

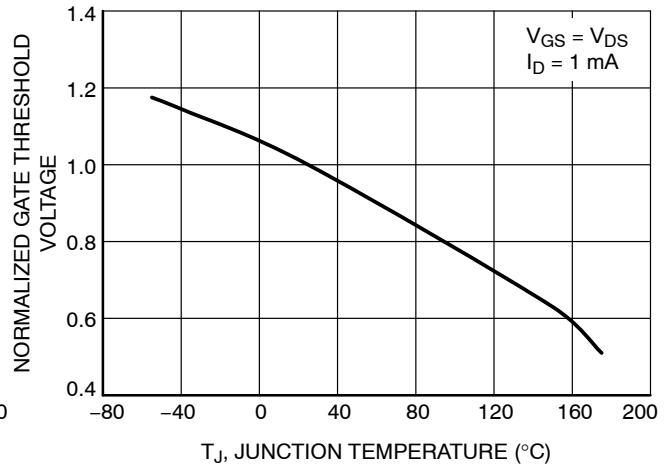


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

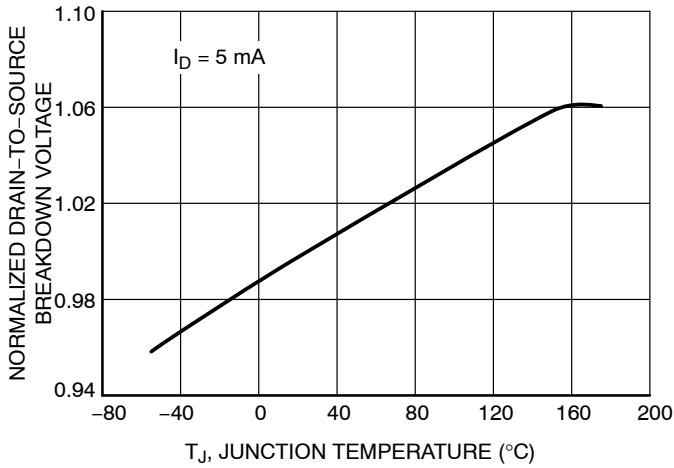


Figure 14. Normalized Drain-to-Source Breakdown Voltage vs. Junction Temperature

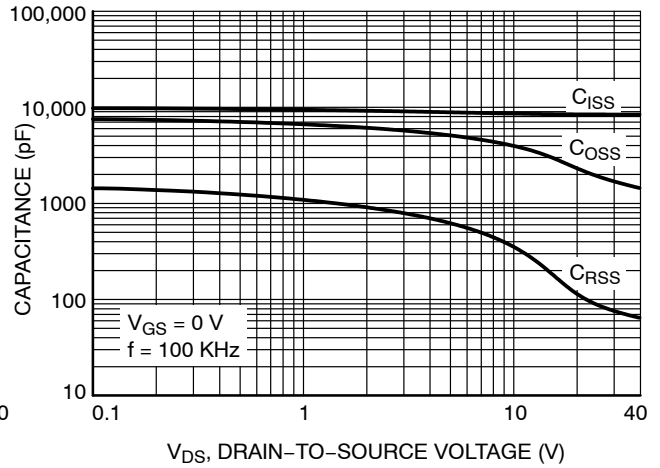


Figure 15. Capacitance vs. Drain-to-Source Voltage

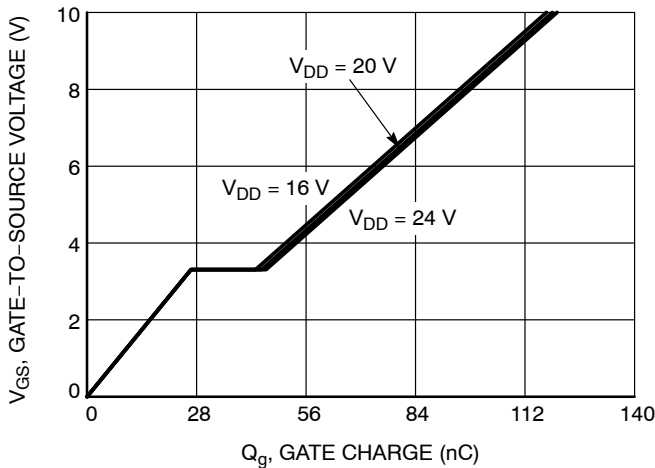


Figure 16. Gate Charge vs. Gate-to-Source Voltage

FDBL9406L-F085

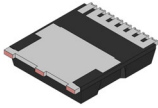
PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Quantity
FDBL9406L-F085	FDBL9406L	H-PSOF8L (Pb-Free / Halogen Free)	13"	24 mm	2000 Units

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

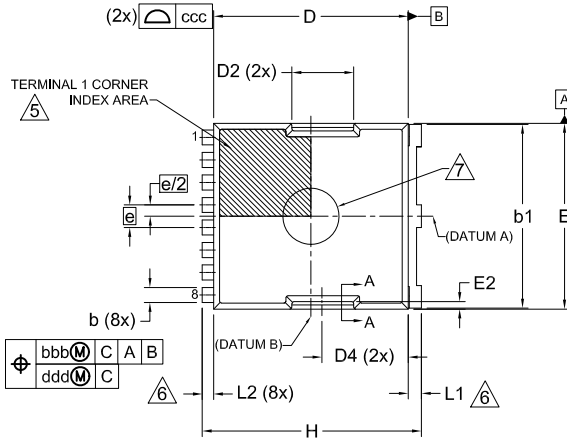
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

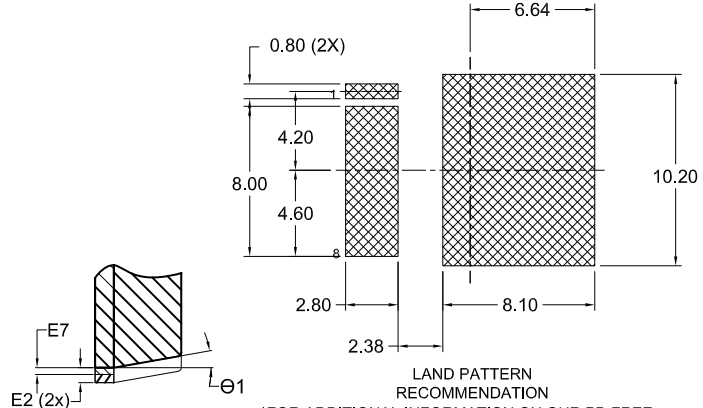


H-PSOF8L 11.68x9.80x2.30, 1.20P
CASE 100CU
ISSUE D

DATE 25 APRIL 2024

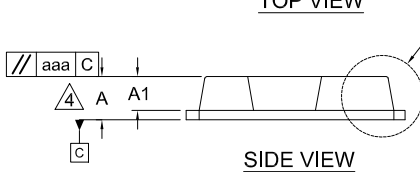


TOP VIEW

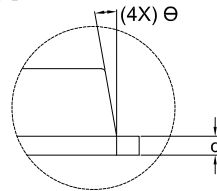


LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



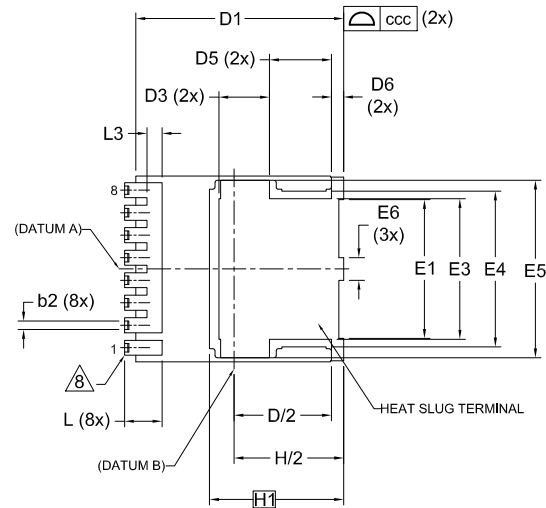
SIDE VIEW



DETAIL "A"
SCALE: 2X

NOTES:

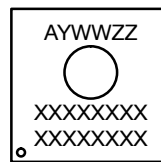
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
3. "e" REPRESENTS THE TERMINAL PITCH.
4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g., EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
6. DIMENSIONS b1, L1, L2 APPLY TO PLATED TERMINALS.
7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.



BOTTOM VIEW

DETAIL "B"
SCALE: 2X

GENERIC MARKING DIAGRAM*



A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code
 XXXX = Specific Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "μ", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	7.40	7.50	7.60
E4	8.20	8.30	8.40

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E5	9.36	9.46	9.47
E6	1.10	1.20	1.30
E7	0.15	0.18	0.21
e	1.20 BSC		
e/2	0.60 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.90	2.00	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.70	0.80	0.90
θ	10° REF		
θ1	10° REF		
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

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DESCRIPTION:	H-PSOF8L 11.68x9.80x2.30, 1.20P	PAGE 1 OF 1

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